**Power Optimization of Linear Feedback Shift Register (LFSR) using Power Gating**

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**Abstract** - In this paper a method to reduce the power consumption of the popular Linear Feedback Shift Register is presented. A traditional 16-bit Linear Feedback Shift Register (LFSR) without power gating technique is implemented and the leakage power report is then compared with LFSR designed using different power gating techniques. In the circuit as the scaling increase the leakage power increases. Out of all the available solutions to reduce leakage power dissipation, power-gating has proved to be efficient in reducing stand-by leakage currents in the idle mode. Power gating is a technique used to reduce the power consumption in integrated circuit design, by shutting off the current to blocks of the circuit that are not in use. The basic element used for shutting down the power in power gating technique is a sleep transistor. The basic idea of power gating is to separate the VDD or GND power supply from the standard cells of the specific design hierarchy. Appropriate sized PMOS or NMOS transistors are used as sleep transistor.

**Key Words:** Power gating, Linear Feedback Shift Register (LFSR), Fine Grain Power Gating (FGPG), Coarse Grain Power Gating (CGPG), Leakage power.

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**1. INTRODUCTION**

Electronic circuits are confronted with the problem of delivering high performance with limited power consumption. Low power consumption is required to increase the battery life of various components and also to reduce many impacts like induced noise cooling and heat dissipation. Electronic circuits are made up of heterogeneous components and at different interval of time they may consume power from the power budget. Dynamic Power Management methodology will reconfigure the system to provide the requested services with minimum number of active components by turning off components in sleep mode [1].

Power dissipation can be mainly classified into dynamic power dissipation and static power dissipation. Dynamic power dissipation is due to switching activity and it contributes to the major power dissipation in VLSI circuits. Various clock gating techniques are used to reduce dynamic power dissipation in circuits. Static power dissipation is due to leakage current and it is very small in VLSI circuits. Power gating techniques are used to reduce leakage power in circuits. Reducing both these power dissipation can reduce the power in circuits. It is difficult to reduce leakage power when the circuit is working or operating. Therefore it is easier to reduce the leakage power during idle or sleep mode of the circuit [2].

In power gating technique a NMOS sleep transistor is inserted between the virtual and actual ground rail and a PMOS sleep transistor is inserted between the virtual and actual Vdd. The input to the sleep transistor can be through a gate control or by a source. The sleep transistor will be turned-on when the circuit is in active mode and in order to reduce the leakage path the sleep transistor will be turned-off during the sleep mode [3].

**2. TRADITIONAL LFSR**

The Linear Feedback Shift Register (LFSR) is a shift register which sequences through \((2^n-1)\) states, where \(n\) is the total number of shift registers used in designing the LFSR [7]. This is achieved by an array of D flip-flops where, XOR or XNOR gates are used for performing linear functions, as given in Fig.1[4], [6]. They are described by the polynomial,

\[
P_n(x) = x^n + b_{n-1}x^{n-1} + \cdots + b_1x + 1
\]  

Where the coefficients denoted as \(b_i\) represents the polynomial characteristic. LFSR exhibits high-speed bit generation and used in pseudo Noise sequences, digital counters etc. High power utilization is the disadvantage of these generators [4], [5]. LFSRs are frequently used as pseudorandom pattern generators to generate a random number of 1s and 0s. There are two types of LFSR's-external feedback LFSR's and internal feedback LFSR's. The maximum-length of an LFSR sequence is \(2^n-1\).

**Fig. -1:** Traditional n-bit LFSR

**3. POWER GATING TECHNIQUES**

**3.1 Fine Grain Power Gating (FGPG)**

Fine Grain Power Gating (FGPF) [8] is a process of inserting a sleep transistor to each cell as shown in Fig.2. Sleep
transistor is added to every cell that is to be turned off imposes a large area penalty and individually gating the power of every cluster of cells creates timing issues introduced by inter-cluster voltage variation, these are very difficult to resolve.

Fig. 2: Fine Grain Power Gating

3.2 Coarse Grain Power Gating (CGPG)

The CGPG [8] Process implements the grid style sleep transistors which drives cells locally through shared virtual ground and virtual \( V_{DD} \) networks. This technique introduces less sensitive to PVT variation & imposes a smaller area overhead than the implementations based on cell- or cluster. In Fig.3 one sleep transistor is added to a cluster of cells.

Fig. 3: Coarse Grain Power Gating

4. IMPLEMENTATION AND RESULTS

D flip-flop and Linear Feedback Shift Register (LFSR) circuits are designed using Cadence Virtuoso tool with 90nm CMOS technology. The transient analysis is done by launching ADEL for verification of schematic results. The power report is obtained for D flip-flop, 16-bit and 32-bit Linear Feedback Shift Register (LFSR) with and without using power gating technique.

4.1 D Flip-Flop

Fig. 4 shows the schematic of 2-input and 3-input NAND gate respectively. These circuits are used to design the D flip-flop without using power gating.

Fig. 4: Schematic of 2-input and 3-input NAND gate

Fig. 5 shows the schematic of D flip-flop without using power gating. Fig. 6 shows the transient response of D flip-flop which is obtained by launching ADEL.

Fig. 5: Schematic of D flip-flop

Fig. 6: Transient response of D flip-flop

Fig. 7 shows the schematic of 2-input NAND gate and 3-input NAND gate where one PMOS and one NMOS sleep transistor is inserted in each NAND circuit respectively. These circuits are used to design the D flip-flop with Fine Grain Power Gating (FGPG).

Fig. 7: Schematic of 2-input NAND gate and 3-input NAND gate
Fig. 7: 2-input and 3-input NAND gate used in D flip-flop with FGPG

Fig. 8 shows the schematic of D flip-flop using Fine Grain Power Gating (FGPG), where one NMOS sleep transistor is inserted between the virtual and actual ground rail of each NAND gate and one PMOS sleep transistor is inserted between the virtual and actual \( VDD \). Fig.9 shows the transient response of D flip-flop which is obtained by launching ADEL.

Fig. 8: Schematic of a D flip-flop with Fine Grain Power Gating

Fig. 9: Transient response of D flip-flop with Fine Grain Power Gating

Fig. 10: 2-input and 3-input NAND gates used in D flip-flop with CGPG

Fig.11 shows the schematic of D flip-flop using Coarse Grain Power Gating (CGPG), where one NMOS sleep transistor is inserted between the virtual and actual ground rail of all the NAND gates and one PMOS sleep transistor is inserted between the actual and virtual \( VDD \). Fig.12 shows the transient response of D flip-flop which is obtained by launching ADEL.

Fig. 11: Schematic of D flip-flop with Coarse Grain Power Gating

Fig. 12: Transient response of D flip-flop with Coarse Grain Power Gating

From Fig.6, Fig.9 and Fig.12 it can be observed that the D flip-flop captures the value of the D-input at a definite portion of the clock cycle (such as the rising edge of the clock). That captured value becomes the Q output. At other times, the output Q does not change.

The advantage of the D flip-flop is that the signal on the D input pin is taken the moment the flip-flop is clocked, and
subsequent changes on the D input will be ignored until the next clock event.

4.2 16-bit Linear Feedback Shift Register

The 16-bit LFSR is designed for the polynomial \(x^{16} + x^{15} + x^{13} + x^4 + 1\). Fig.13 shows the schematic for 16-bit LFSR, where the 16-bit LFSR is designed using D flip-flop without using power gating as shown in Fig.5. Fig.14 shows the transient response of 16-bit LFSR.

Fig. 13: Schematic of 16-bit LFSR

Fig. 14: Transient response of 16-bit LFSR

Fig.15 shows the schematic for 16-bit LFSR with Fine Grain Power Gating (FGPG) technique, where the LFSR is designed using power gated D flip-flops as shown in Fig.8 and XOR gates. Fig.16 shows the transient response of 16-bit LFSR using FGPG.

Fig. 15: Schematic of 16-bit LFSR with Fine Grain Power Gating

Fig. 16: Transient response of 16-bit LFSR with Fine Grain Power Gating

Fig.17 shows the schematic for 16-bit LFSR with Coarse Grain Power Gating (CGPG) technique, where the LFSR is designed using power gated D flip-flops as shown in Fig.11 and XOR gates. Fig.18 shows the transient response of 16-bit LFSR using CGPG.

Fig. 17: Schematic of 16-bit LFSR with Coarse Grain Power Gating

Fig. 18: Transient response of 16-bit LFSR with Coarse Grain Power Gating

The 16-bit Linear Feedback Shift Register (LFSR) sequences through \((2^{16}-1)\) states, where 16 is the total number of shift registers used in designing the LFSR. This is achieved by an array of D flip-flop where, XOR gates are used to perform linear functions. The maximum-length of an LFSR sequence is 216-1. It can be observed from Fig.14, Fig.16 and...
Fig. 18 that the sequence repeats after every 65,535 clock cycles.

5. POWER ANALYSIS

The Leakage power dissipation is calculated using Cadence tool Calculator.

Table 1 shows the leakage power of a normal D flip-flop and also power gated D flip-flop’s with Fine Grain Power Gating (FGPG) and Coarse Grain Power Gating (CGPG) techniques. There is 23.90% leakage power reduction in D flip-flop implemented using Fine Grain Power Gating (FGPG) technique and 55.20% leakage power reduction in D flip-flop implemented using Coarse Grain Power Gating (CGPG) technique compared to the normal D flip-flop.

Table 1: Power analysis of D Flip-Flop

<table>
<thead>
<tr>
<th>D flip-flop</th>
<th>Maximum Leakage Power Dissipation</th>
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</thead>
<tbody>
<tr>
<td>D flip-flop without gating</td>
<td>35.60 uW</td>
</tr>
<tr>
<td>D flip-flop with Fine Grain Power Gating</td>
<td>27.09 uW</td>
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<tr>
<td>D flip-flop with Coarse Grain Power Gating</td>
<td>15.92 uW</td>
</tr>
</tbody>
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Table 2 shows the leakage power of a normal 16-bit LFSR and also power gated 16-bit LFSR implemented using D flip-flop’s with Fine Grain Power Gating (FGPG) and Coarse Grain Power Gating (CGPG) techniques. There is 38.15% leakage power reduction in 16-bit LFSR implemented using Fine Grain Power Gating (FGPG) technique and 74.2% leakage power reduction in 16-bit LFSR implemented using Coarse Grain Power Gating (CGPG) technique compared to the normal 16-bit LFSR.

Table 2: Power analysis of 16-bit LFSR

<table>
<thead>
<tr>
<th>16-bit LFSR</th>
<th>Maximum Leakage Power Dissipation</th>
</tr>
</thead>
<tbody>
<tr>
<td>16-bit LFSR without gating</td>
<td>688.2 uW</td>
</tr>
<tr>
<td>16-bit LFSR with Fine Grain Power Gating</td>
<td>425.6 uW</td>
</tr>
<tr>
<td>16-bit LFSR with Coarse Grain Power Gating</td>
<td>177.5 uW</td>
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Table 3 show the leakage power of normal D flip-flop and 16-bit LFSR has been compared with the power gated D flip-flop and 16-bit LFSR, it is observed that there is leakage power reduction in the power gated circuits when compared to the normal circuits.

Linear Feedback Shift Register with higher order bits can be used to generate pseudorandom test vectors. High fault coverage can be obtained by using more test vectors. Hardware used for LFSR is less and hence it is a preferable for BIST pattern generation.

REFERENCES


